

1. General description

Planar passivated Silicon Controlled Rectifier in a SOT429N (TO-247) plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{j(max)} = 150\text{ °C}$).

2. Features and benefits

- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- Very high current surge capability
- Planar passivated for voltage ruggedness and reliability
- High thermal cycling performance
- High voltage capability

3. Applications

- Line rectifying 50/60 Hz
- Soft start AC motor control
- DC motor control
- Power converter
- AC power control
- Lighting and temperature control
- Uninterruptible Power Supply (UPS)
- Solid State Relay (SSR)
- Traction battery charging

4. Quick reference data

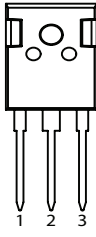

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute maximum rating				
V_{DRM}	repetitive peak off-state voltage		1600	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 127\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	79	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	650	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	715	A
T_j	junction temperature		150	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7 ; Fig. 8	-	-	80	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	-	200	mA
V_T	on-state voltage	$I_T = 50\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	-	1.3	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 1070\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	1500	-	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>TO-247 (SOT429N)</p>	 <p>sym037</p>
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
TYN50W-1600T	TO-247	Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247	SOT429N

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		1600	V
V_{RRM}	repetitive peak reverse voltage		1600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 127^{\circ}\text{C}$;	50	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 127^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	79	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	650	A
		half sine wave; $T_{j(\text{init})} = 25^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	715	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine wave	2112	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 200\text{ mA}$	150	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		8	A
V_{RGM}	peak reverse gate voltage		5	V
P_{GM}	peak gate power		20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	1	W
T_{stg}	storage temperature		-40 to 150	$^{\circ}\text{C}$
T_j	junction temperature		150	$^{\circ}\text{C}$

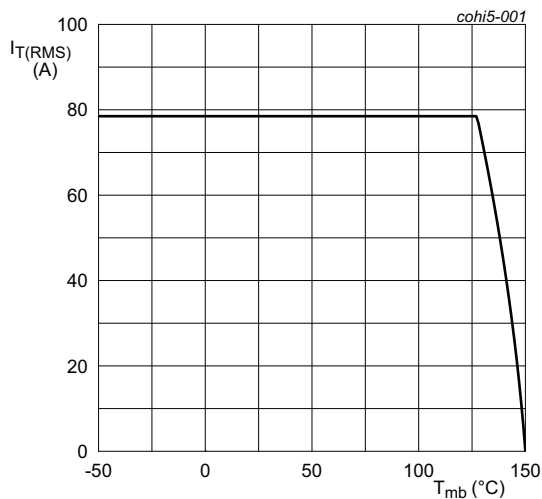
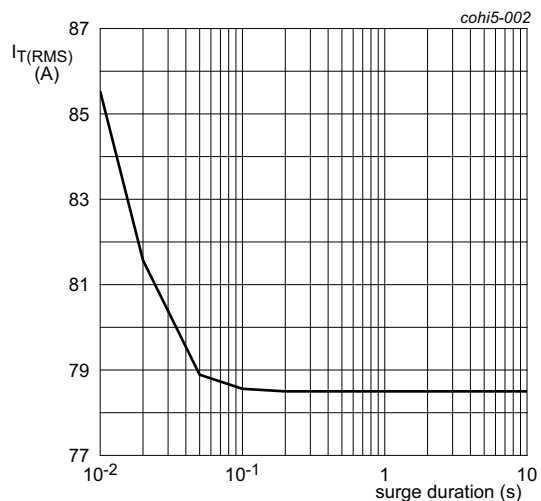


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$; $T_{mb} = 127^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

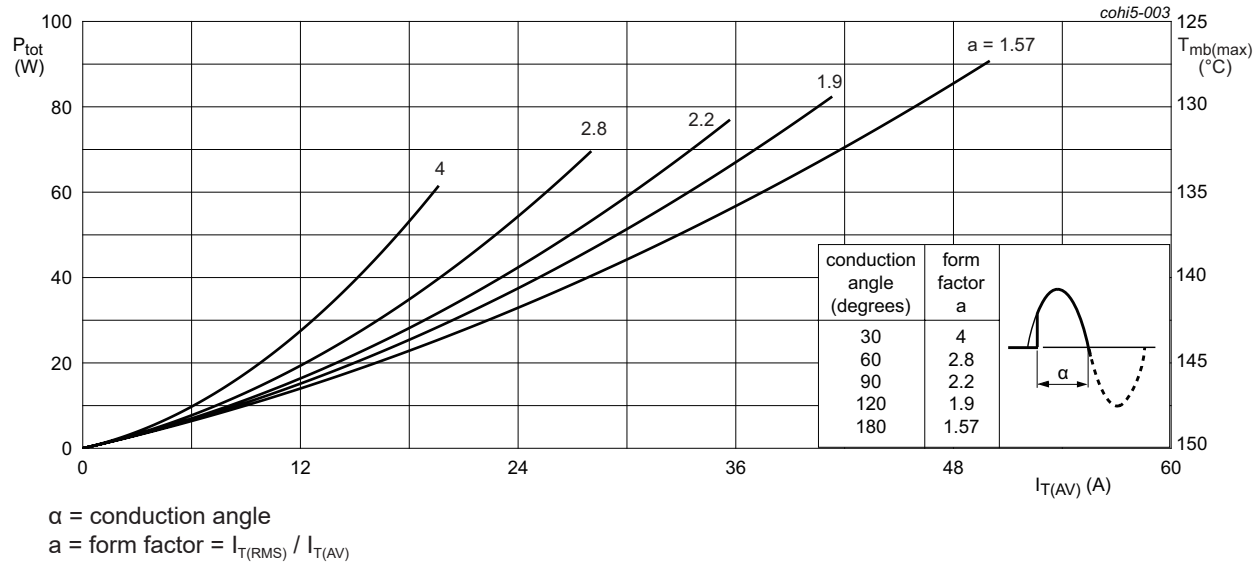


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

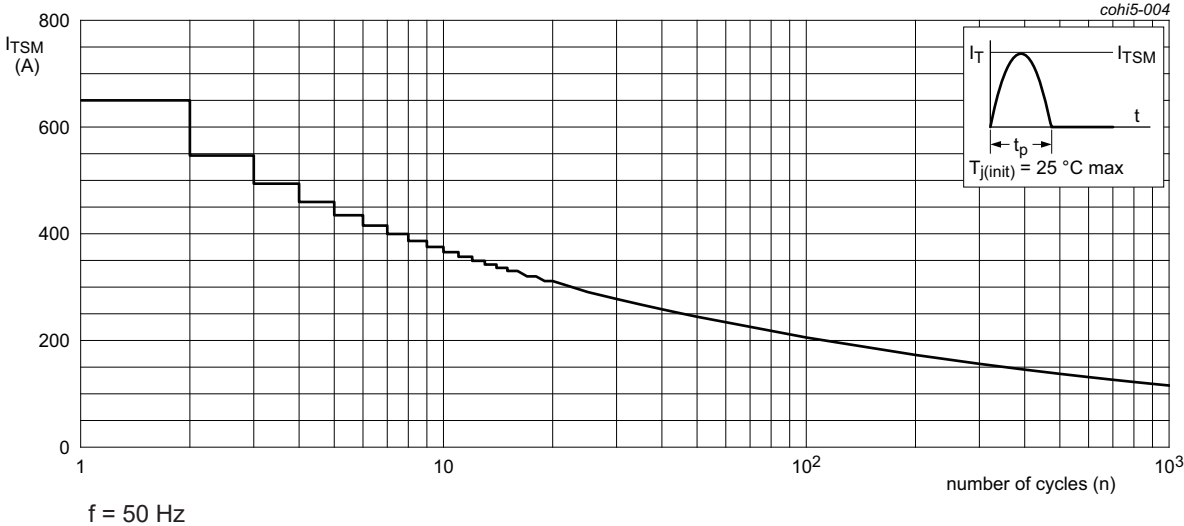


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

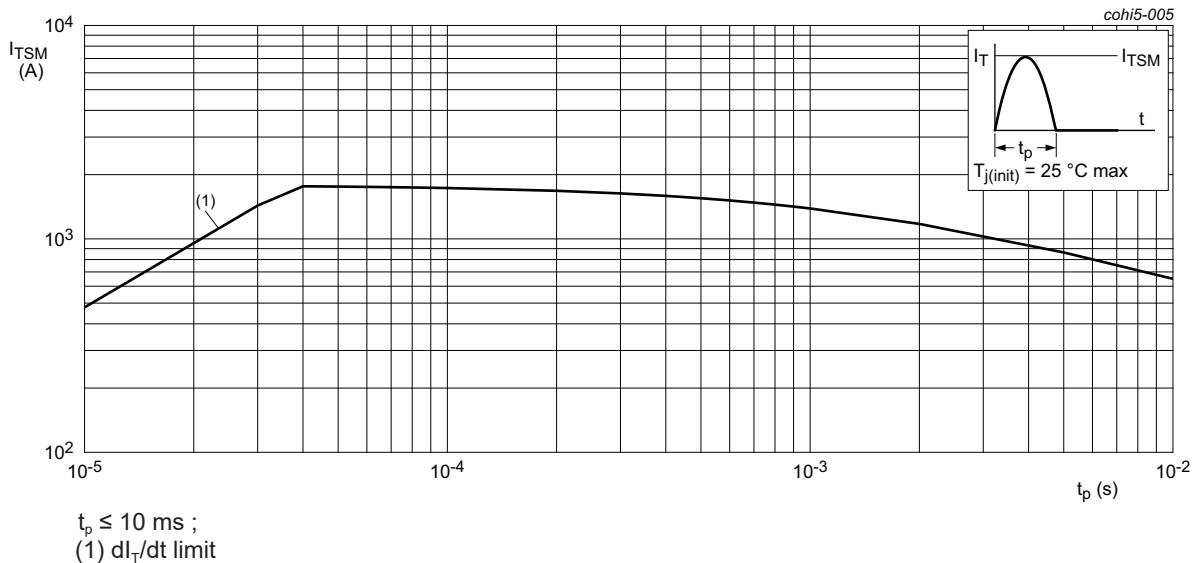
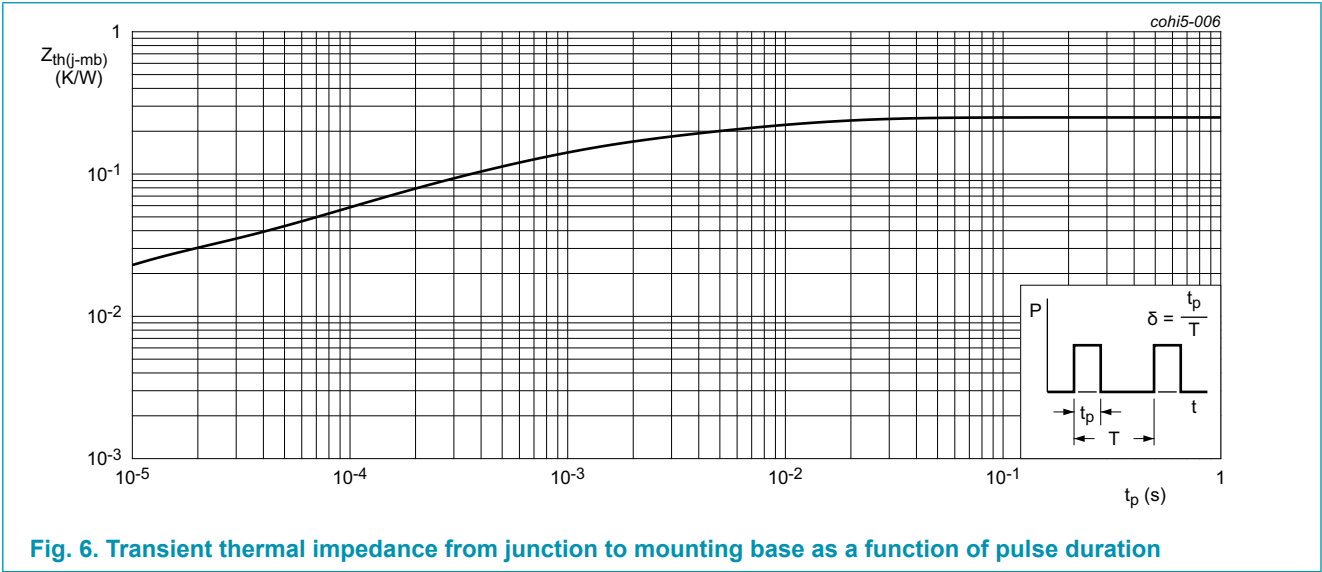


Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6		-	-	0.25	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	50	-	K/W



9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7 ; Fig. 8		-	-	80	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 9		-	-	300	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 10		-	-	200	mA
V_T	on-state voltage	$I_T = 50\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11		-	-	1.3	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12		-	0.7	1	V
		$V_D = 800\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$; Fig. 12		0.25	0.4	-	V
I_D	off-state current	$V_D = 1600\text{ V}$; $T_j = 125\text{ °C}$		-	-	3	mA
I_R	reverse current	$V_D = 1600\text{ V}$; $T_j = 125\text{ °C}$		-	-	3	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 1070\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		2000	-	-	V/ μ s
		$V_{DM} = 1070\text{ V}$; $T_j = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		1500	-	-	V/ μ s
t_{gt}	gate-controlled turn-on time	$I_{TM} = 40\text{ A}$; $V_D = 800\text{ V}$; $I_G = 100\text{ mA}$; $(dI_G/dt)_M = 0.5\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$			2	-	μ s
t_q	commutated turn-off time	$V_{DM} = 1070\text{ V}$; $T_j = 125\text{ °C}$; $I_{TM} = 50\text{ A}$; $V_R = 25\text{ V}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$; ($V_{DM} = 67\%$ of V_{DRM})			150	-	μ s

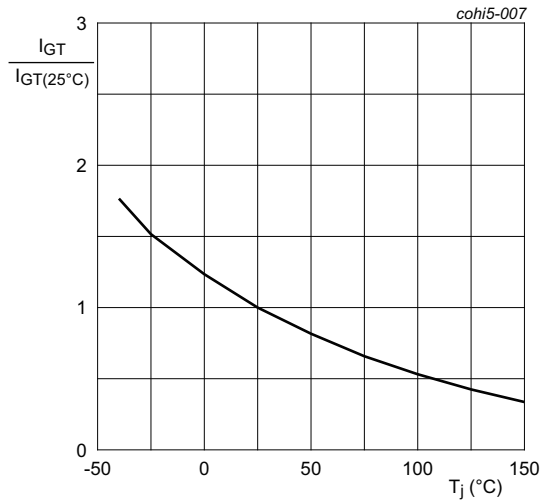


Fig. 7. Normalized gate trigger current as a function of junction temperature

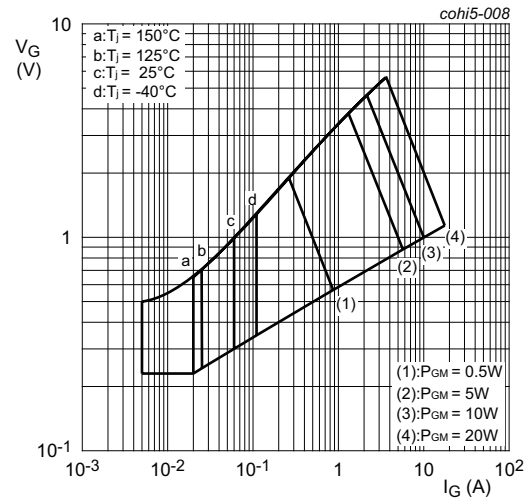


Fig. 8. Gate voltage as a function of gate current

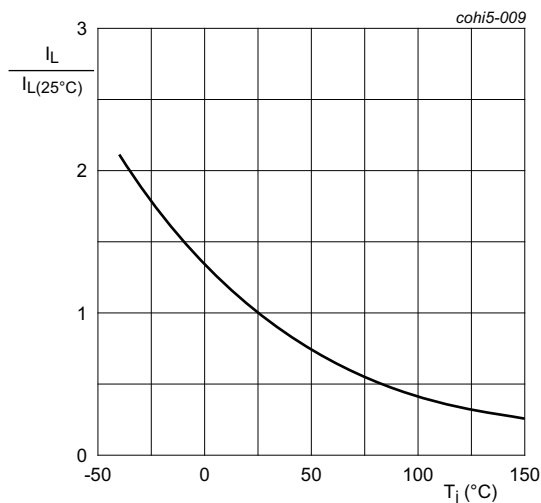


Fig. 9. Normalized latching current as a function of junction temperature

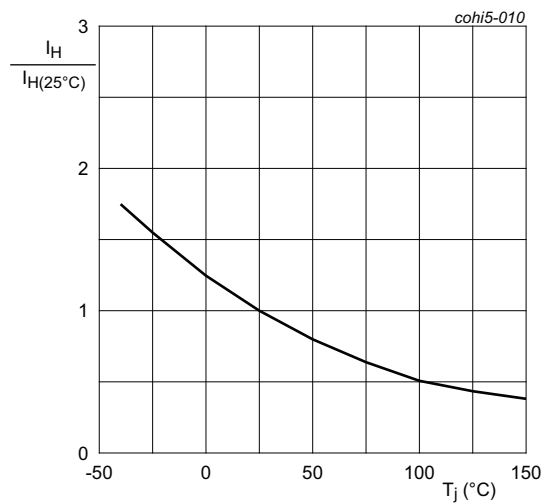
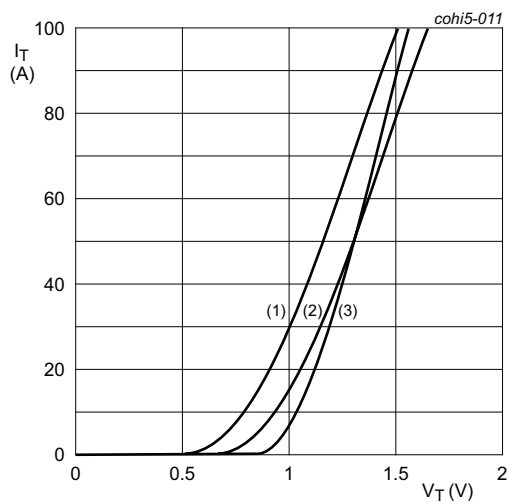


Fig. 10. Normalized holding current as a function of junction temperature



$V_o = 0.963 \text{ V}$; $R_s = 0.0069 \Omega$
 (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 11. On-state current as a function of on-state voltage

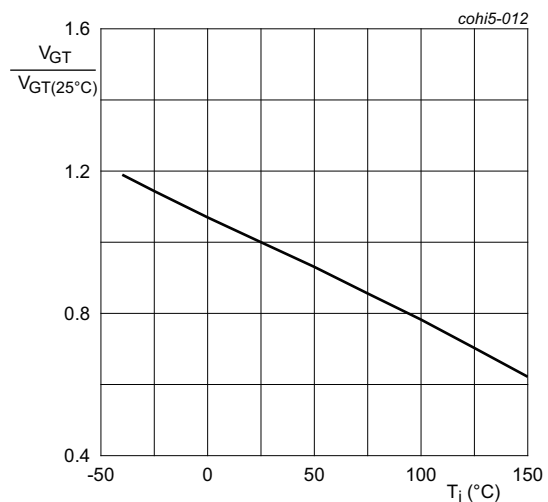
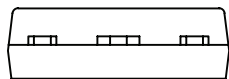
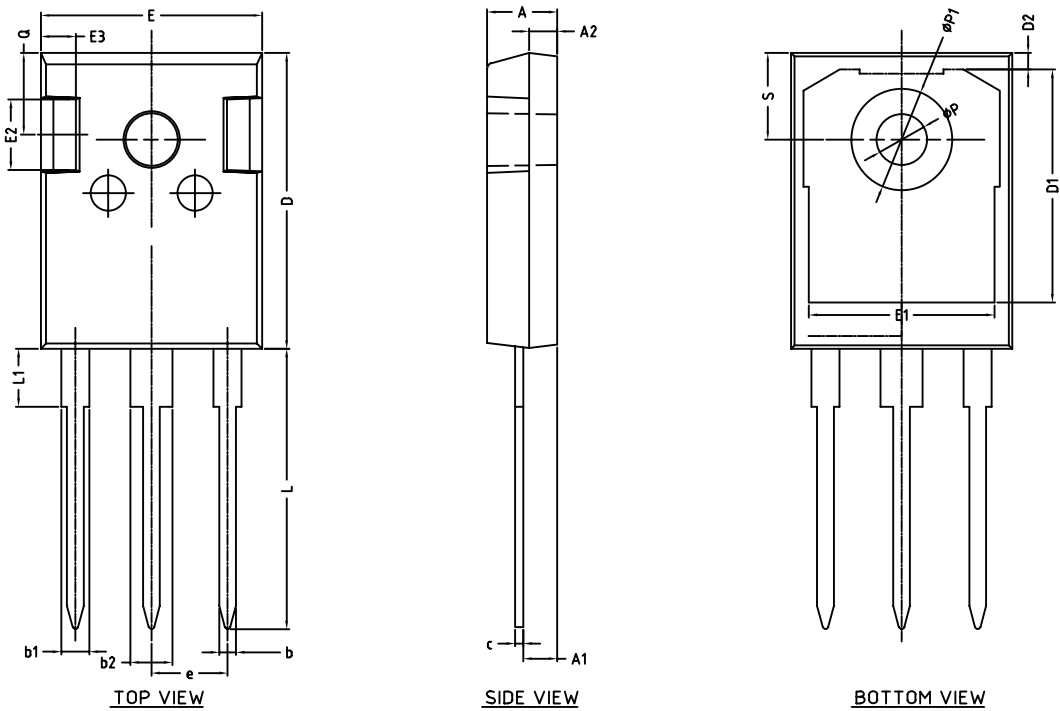


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 SOT429N



SIDE VIEW

UNIT	A	A1	A2	b	b1	b2	c	D	D1	D2	E	E1	E2	E3	e	L	L1	P	P1	Q	S
mm	5.20	2.60	2.10	1.40	2.20	3.20	0.70	21.10	16.85	1.35	15.90	13.50	5.20	2.60	5.45	20.10	4.75	3.70	7.40	6.00	6.25
	4.70	2.20	1.90	1.00	1.80	2.80	0.50	20.90	16.25	1.05	15.70	13.10	4.80	2.40		19.80	-	3.50	-	5.60	6.05

OUTLINE VERSION	REFERENCES				PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT429N		TO-247				

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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